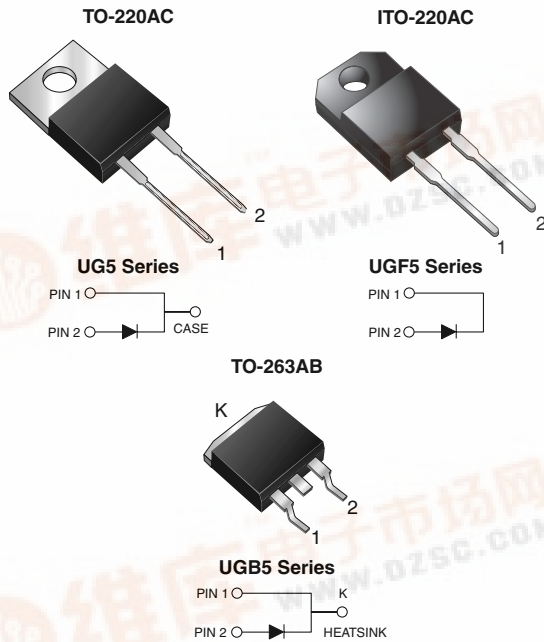




UG(F,B)5HT & UG(F,B)5JT

Vishay General Semiconductor

High Voltage Ultrafast Rectifier



FEATURES

- Glass passivated chip junction
- Ultrafast recovery time
- Soft recovery characteristics
- Low switching losses, high efficiency
- High forward surge capability
- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C (for TO-263AB package)
- Solder dip 260 °C, 40 s (for TO-220AC and ITO-220AC package)
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC



RoHS
COMPLIANT

TYPICAL APPLICATIONS

For use in high voltage and high frequency power factor corrector, freewheeling diodes and secondary dc-to-dc rectification application.

MECHANICAL DATA

Case: TO-220AC, ITO-220AC, TO-263AB

Epoxy meets UL 94V-0 flammability rating

Terminals: Matte tin plated leads, solderable per J-STD-002 and JESD22-B102

E3 suffix for consumer grade, meets JESD 201 class 1A whisker test, HE3 suffix for high reliability grade (AEC Q101 qualified), meets JESD 201 class 2 whisker test

Polarity: As marked

Mounting Torque: 10 in-lbs maximum

PRIMARY CHARACTERISTICS

$I_{F(AV)}$	5.0 A
V_{RRM}	500 V, 600 V
I_{FSM}	65 A
t_{rr}	25 ns
V_F	1.5 V
$T_J \text{ max.}$	150 °C

MAXIMUM RATINGS ($T_C = 25$ °C unless otherwise noted)

PARAMETER	SYMBOL	UG5HT	UG5JT	UNIT
Maximum repetitive peak reverse voltage	V_{RRM}	500	600	V
Maximum working reverse voltage	V_{RWM}	400	480	V
Maximum RMS voltage	V_{RMS}	350	420	V
Maximum DC blocking voltage	V_{DC}	500	600	V
Maximum average forward rectified current	$I_{F(AV)}$	5.0		A
Peak forward surge current 8.3 ms single half sine-wave superimposed on rated load	I_{FSM}	65		A
Operating junction and storage temperature range	T_J, T_{STG}	- 55 to + 150		°C
Isolation voltage (ITO-220AB only) from terminals to heatsink $t = 1$ min	V_{AC}	1500		V

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ELECTRICAL CHARACTERISTICS (T _C = 25 °C unless otherwise noted)						
PARAMETER	TEST CONDITIONS		SYMBOL	UG5HT	UG5JT	UNIT
Maximum instantaneous forward voltage ⁽¹⁾	I _F = 5 A I _F = 5 A	T _J = 25 °C T _J = 125 °C	V _F	1.75 1.50		V
Maximum DC reverse current at V _{RWM}		T _J = 25 °C T _J = 100 °C T _J = 125 °C	I _R	30 800 4.0		μA μA mA
Maximum reverse recovery time	I _F = 0.5 A, I _R = 1.0 A, I _{rr} = 0.25 A		t _{rr}	25		ns
Maximum reverse recovery time	I _F = 1.0 A, dI/dt = 50 A/μs, V _R = 30 V, I _{rr} = 0.1 I _{RM}		t _{rr}	50		ns
Typical softness factor (t _b /t _a)	I _F = 5.0 A, dI/dt = 240 A/μs, V _R = 400 V, I _{rr} = 0.1 I _{RM}		S	0.9		-
Maximum reverse recovery current	I _F = 5.0 A, dI/dt = 40 A/μs, V _R = 400 V, T _C = 125 °C		I _{RM}	3.0		A
Maximum reverse recovery current	I _F = 5.0 A, dI/dt = 240 A/μs, V _R = 400 V, T _C = 125 °C		I _{RM}	9.0		A
Peak forward recovery time	I _F = 5.0 A, dI/dt = 64 A/μs, V _F = 1.1 V _{F max.}		t _{fr}	500		ns

THERMAL CHARACTERISTICS ($T_C = 25\text{ }^{\circ}\text{C}$ unless otherwise noted)					
PARAMETER	SYMBOL	UG5	UGF5	UGB5	UNIT
Typical thermal resistance from junction to case	$R_{\theta JC}$	3.0	5.5	3.0	$^{\circ}\text{C}/\text{W}$

Note:

(1) Pulse test: 300 μs pulse width, 1 % duty cycle

ORDERING INFORMATION (Example)					
PACKAGE	PREFERRED P/N	UNIT WEIGHT (g)	PACKAGE CODE	BASE QUANTITY	DELIVERY MODE
TO-220AC	UG5JT-E3/45	1.80	45	50/tube	Tube
ITO-220AC	UGF5JT-E3/45	1.95	45	50/tube	Tube
TO-263AB	UGB5JT-E3/45	1.33	45	50/tube	Tube
TO-263AB	UGB5JT-E3/81	1.33	81	800/reel	Tape reel
TO-220AC	UG5JT-E3/45 ⁽¹⁾	1.80	45	50/tube	Tube
ITO-220AC	UGF5JT-E3/45 ⁽¹⁾	1.95	45	50/tube	Tube
TO-263AB	UGB5JT-E3/45 ⁽¹⁾	1.33	45	50/tube	Tube
TO-263AB	UGB5JT-E3/81 ⁽¹⁾	1.33	81	800/reel	Tape reel

Note:

(1) Automotive grade AEC Q101 qualified



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RATINGS AND CHARACTERISTICS CURVES

($T_A = 25^\circ\text{C}$ unless otherwise noted)

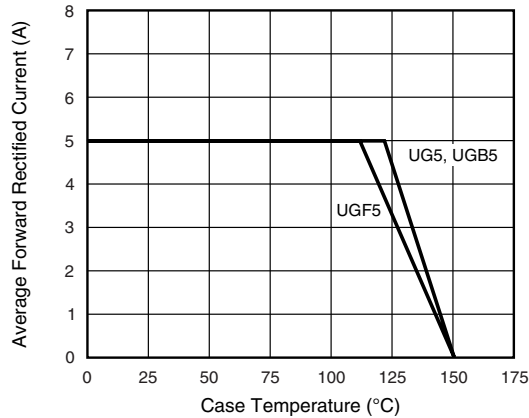


Figure 1. Forward Current Derating Curve

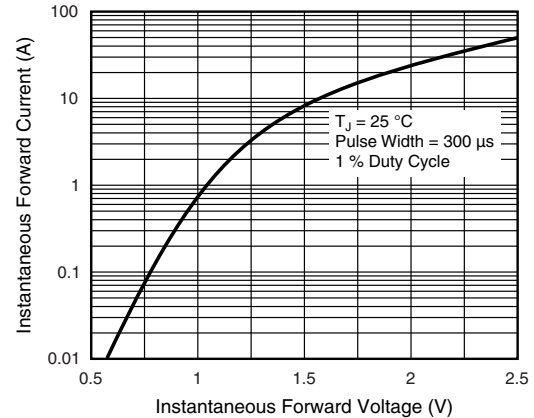


Figure 4. Typical Instantaneous Forward Characteristics

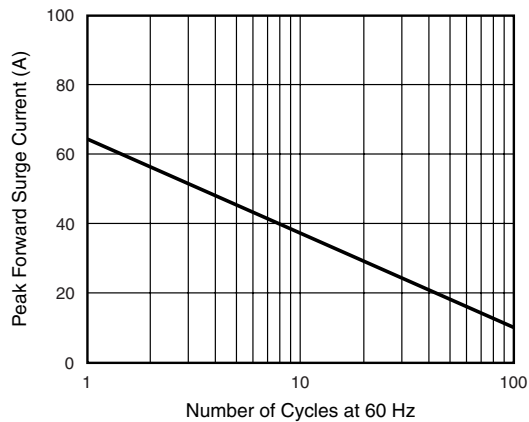


Figure 2. Maximum Non-Repetitive Peak Forward Surge Current

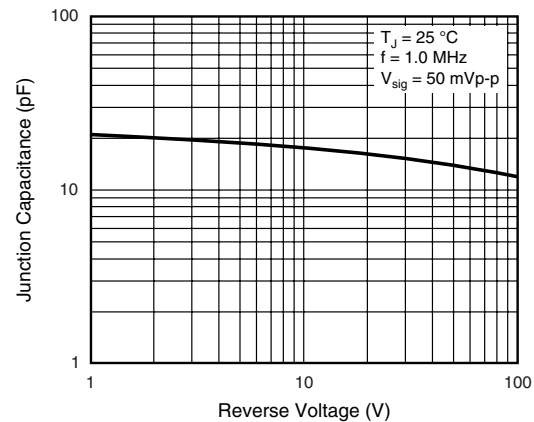


Figure 5. Typical Junction Capacitance

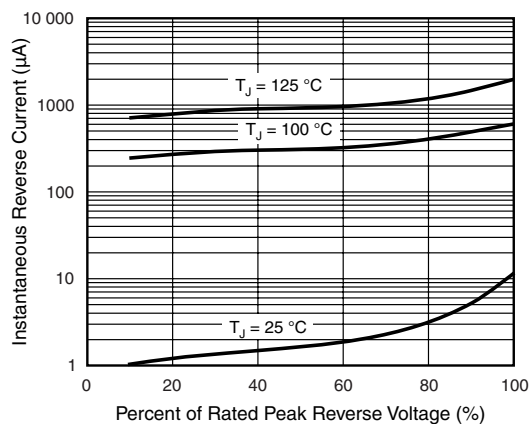


Figure 3. Typical Reverse Characteristics

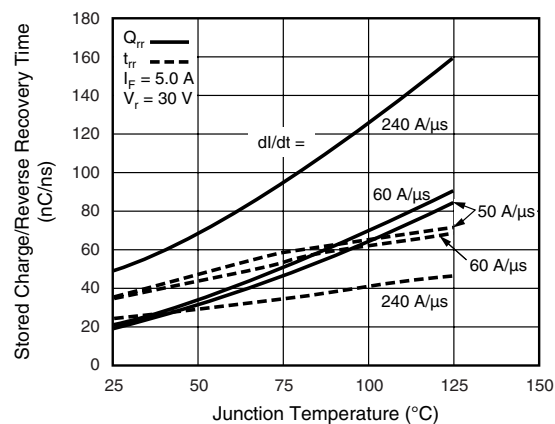


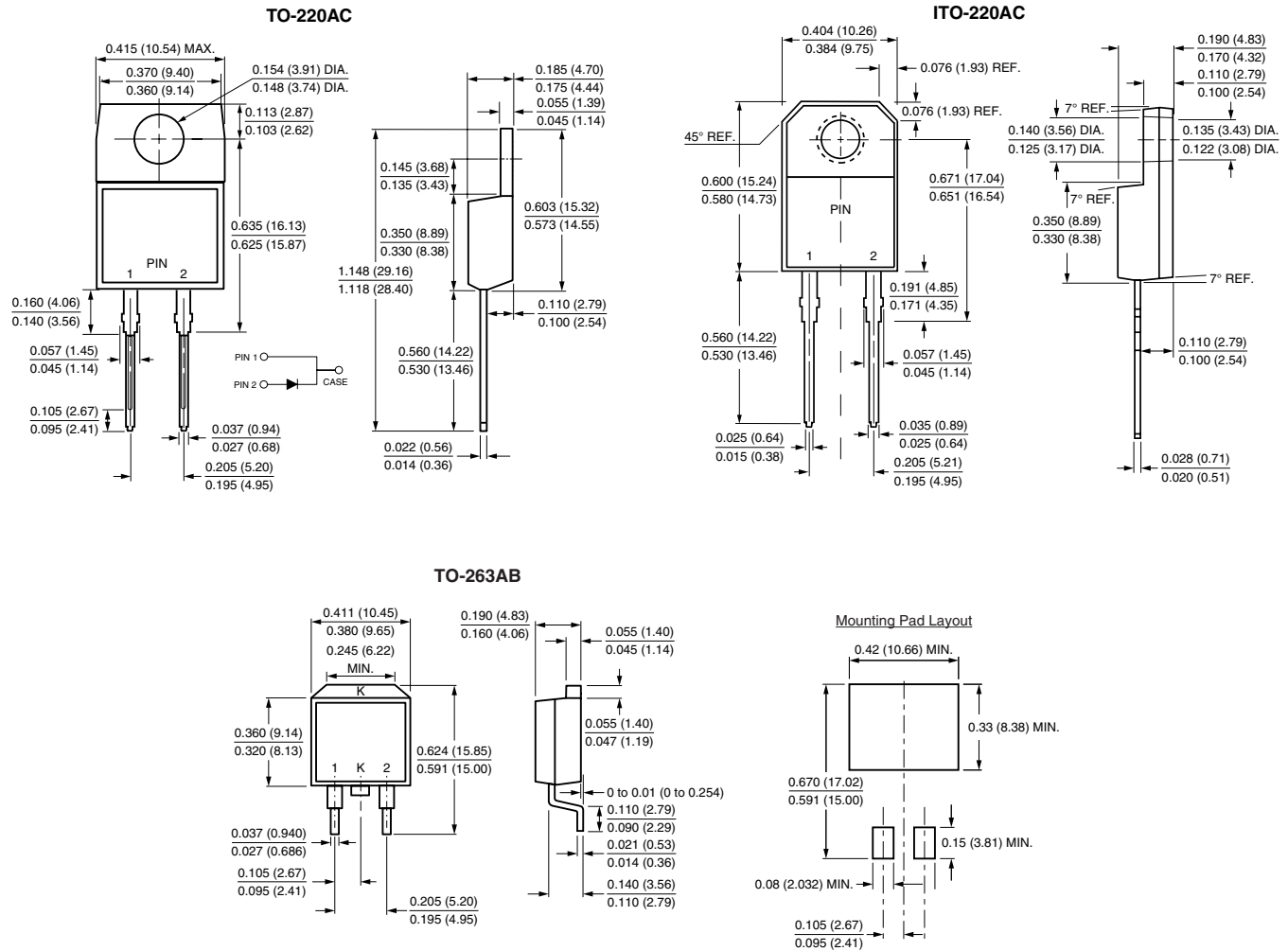
Figure 6. Reverse Switching Characteristics

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PACKAGE OUTLINE DIMENSIONS in inches (millimeters)





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